Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (DTMOS)

TK12X60U

Switching Regulator Applications

• Low drain-source ON resistance: RDS (ON) = 0.36 (typ.)

• High forward transfer admittance: $|Y_{fs}| = 7.0 \text{ S (typ.)}$

• Low leakage current: IDSS = 100 µ A (VDS = 600 V)

• Enhancement-mode: $V_{th} = 3.0 \sim 5.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_{D} = 1 \text{ mA}$)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	600	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	I _D	12		
	Pulse (t = 1 ms) (Note 1)	I _{DP}	24	Α	
Drain power dissipation (Tc = 25°C)		PD	100	W	
Single pulse avalanche energy (Note 2)		E _{AS}	69	mJ	
Avalanche current (Note 3)		I _{AR}	12	Α	
Repetitive avalanche energy		E _{AR}	10	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

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Weight: 0.74 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

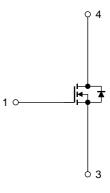
Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to case	R _{th (ch-c)}	1.25	°C/W	

Note 1: Please use devices on conditions that the channel temperature is below 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 0.84 mH, R_G = 25 , I_{AR} = 12 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.



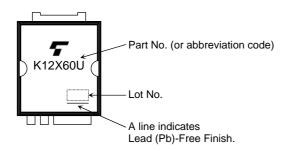
Electrical Characteristics (Ta = 25°C)

Char	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μА
Drain cut-off current		I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	100	μА
Drain-source bre	akdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	600	_		V
Gate threshold v	oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	3.0	_	5.0	V
Drain-source ON	resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 6 A		0.36	0.4	Ω
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 6 A	2.0	7.0		S
Input capacitance		C _{iss}			720		pF
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		55		
Output capacitance		C _{oss}		_	1700		
Switching time	Rise time	t _r	$\begin{array}{c c} 10 \text{ V} & \text{ID} = 6\text{A} & \text{VOUT} \\ \hline \text{VGS} & \text{O} & \text{V} & \text{RL} = \\ 50 \Omega & \text{VDD} \approx 300 \text{ V} \end{array}$		30		
	Turn-on time	t _{on}			60		ns
	Fall time	t _f			8		
	Turn-off time	t _{off}	Duty ≦ 1%, t _W = 10 μs	_	75	_	
Total gate charge		Qg		_	14	_	
Gate-source charge		Q _{gs}	$V_{DD} \simeq 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 12 \text{ A}$	_	8.5	_	nC
Gate-drain charge		Q _{gd}		_	5.5	_	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1	I _{DR}	_	_	_	12	Α
Pulse drain reverse current (Note 1	I _{DRP}	_	_	_	24	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 12 A, V _{GS} = 0 V	_	_	-1.7	٧
Reverse recovery time	t _{rr}	I _{DR} = 12 A, V _{GS} = 0 V,	_	380	_	ns
Reverse recovery charge	Q _{rr}	dI _{DR} /dt = 100 A/μs	_	5.3	_	μС

Marking



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20070701-EN

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